



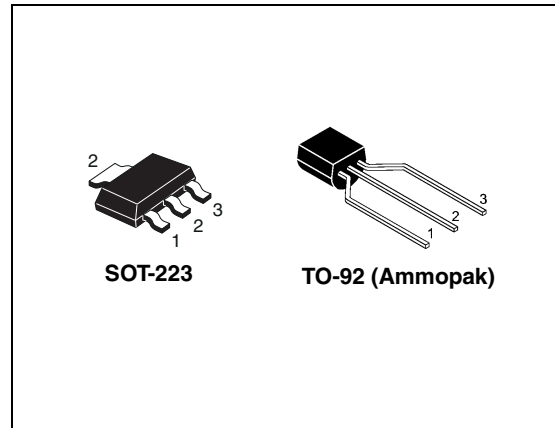
# STN1NK60Z STQ1NK60ZR-AP

N-channel 600 V, 13  $\Omega$  0.8 A TO-92, SOT-223  
Zener-protected SuperMESH™ Power MOSFET

## Features

Order codes	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>	P <sub>w</sub>
STQ1NK60ZR-AP	600 V	< 15 $\Omega$	0.3 A	3 W
STN1NK60Z				3.3 W

- 100% avalanche tested
- Extremely high dv/dt capability
- Gate charge minimized
- ESD improved capability
- New high voltage benchmark



## Application

Switching applications

## Description

This device is a N-channel SuperMESH™ that is obtained through an optimization of STMicroelectronics' well-established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly lower, it also ensures very good dv/dt capability for the most demanding applications. This series complement STs' full range of high voltage Power MOSFETs.

Figure 1. Internal schematic diagram

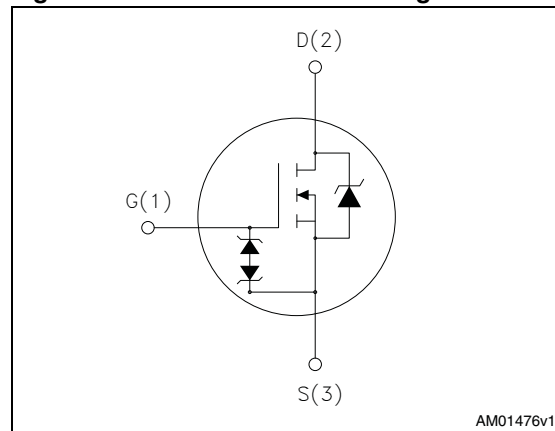


Table 1. Device summary

Order codes	Marking	Package	Packaging
STQ1NK60ZR-AP	1NK60ZR	TO-92	Ammopak
STN1NK60Z	1NK60Z	SOT-223	Tape and reel

## Contents

<b>1</b>	<b>Electrical ratings</b> .....	<b>3</b>
<b>2</b>	<b>Electrical characteristics</b> .....	<b>4</b>
	2.1 Electrical characteristics (curves) .....	6
<b>3</b>	<b>Test circuit</b> .....	<b>9</b>
<b>4</b>	<b>Package mechanical data</b> .....	<b>10</b>
<b>5</b>	<b>Revision history</b> .....	<b>15</b>

# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value		Unit
		TO-92	SOT-223	
$V_{DS}$	Drain-source voltage ( $V_{GS} = 0$ )	600		V
$V_{GS}$	Gate-source voltage	$\pm 30$		V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	0.3	0.3	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	0.189		A
$I_{DM}^{(1)}$	Drain current (pulsed)	1.2		A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	3	3.3	W
	Derating factor	0.25	0.26	W/ $^\circ\text{C}$
$V_{ESD(G-D)}$	Gate source ESD (HBM-C=100 pF, R=1.5 k $\Omega$ )	800		V
$dv/dt^{(2)}$	Peak diode recovery voltage slope	4.5		V/ns
$T_J$ $T_{stg}$	Operating junction temperature Storage temperature	- 55 to 150		$^\circ\text{C}$

1. Pulse width limited by safe operating area
2.  $I_{SD} \leq 0.3\text{ A}$ ,  $di/dt \leq 200\text{ A}/\mu\text{s}$ ,  $V_{DD} = 80\%V_{(BR)DSS}$

**Table 3. Thermal resistance**

Symbol	Parameter	Value		Unit
		TO-92	SOT-223	
$R_{thj-a}$	Thermal resistance junction-ambient max	120	38 <sup>(1)</sup>	$^\circ\text{C}/\text{W}$
$R_{thj-lead}$	Thermal resistance junction-lead max	40		$^\circ\text{C}/\text{W}$
$T_l$	Maximum lead temperature for soldering purpose	260		$^\circ\text{C}$

1. When mounted on 1 inch<sup>2</sup> FR-4 board, 2 Oz Cu,  $t < 30\text{ s}$ .

**Table 4. Avalanche data**

Symbol	Parameter	Value	Unit
$I_{AR}$	Avalanche current, repetitive or not-repetitive (pulse width limited by $T_J$ Max)	0.8	A
$E_{AS}$	Single pulse avalanche energy (starting $T_J = 25\text{ }^\circ\text{C}$ , $I_D = I_{AR}$ , $V_{DD} = 50\text{ V}$ )	60	mJ

## 2 Electrical characteristics

( $T_{CASE} = 25\text{ °C}$  unless otherwise specified)

**Table 5. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$ , $V_{GS} = 0$	600			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = \text{max rating}$ , $V_{DS} = \text{max rating @ } 125\text{ °C}$			1 50	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20\text{ V}$			$\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 50\text{ }\mu\text{A}$	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$ , $I_D = 0.4\text{ A}$		13	15	$\Omega$

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15\text{ V}$ , $I_D = 0.4\text{ A}$		0.5		S
$C_{iss}$	Input capacitance	$V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0$		94		pF
$C_{oss}$	Output capacitance			17.6		pF
$C_{rss}$	Reverse transfer capacitance			2.8		pF
$C_{oss\text{ eq}}^{(2)}$	Equivalent output capacitance	$V_{GS} = 0$ , $V_{DS} = 0\text{ to } 480\text{ V}$		11		pF
$Q_g$	Total gate charge	$V_{DD} = 480\text{ V}$ , $I_D = 0.8\text{ A}$		4.9	6.9	nC
$Q_{gs}$	Gate-source charge	$V_{GS} = 10\text{ V}$		1		nC
$Q_{gd}$	Gate-drain charge	(see Figure 19)		2.7		nC

1. Pulsed: pulse duration=300 $\mu\text{s}$ , duty cycle 1.5%

2.  $C_{oss\text{ eq}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}$ , $I_D = 0.4\text{ A}$ , $R_G = 4.7\ \Omega$ , $V_{GS} = 10\text{ V}$ (see Figure 18)		5.5		ns
$t_r$	Rise time			5		ns
$t_{d(off)}$	Turn-off delay time			13		ns
$t_f$	Fall time			28		ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
$I_{SD}$	Source-drain current				0.8	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				2.4	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 0.8\text{ A}$ , $V_{GS} = 0$			1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 0.8\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 20\text{ V}$		135		ns
$Q_{rr}$	Reverse recovery charge			216		nC
$I_{RRM}$	Reverse recovery current			3.2		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 0.8\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 20\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$		140		ns
$Q_{rr}$	Reverse recovery charge			224		nC
$I_{RRM}$	Reverse recovery current			3.2		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300 $\mu\text{s}$ , duty cycle 1.5%

Table 9. Gate-source Zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$BV_{GSO}^{(1)}$	Gate-source breakdown voltage	$I_{GS} = \pm 1\text{ mA}$ (open drain)	30			V

1. The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-92

Figure 3. Thermal impedance for TO-92

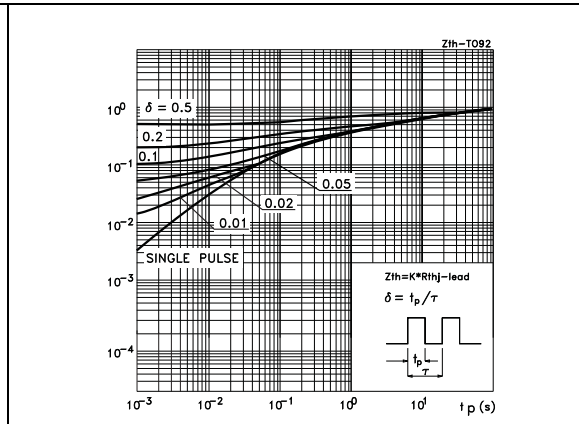
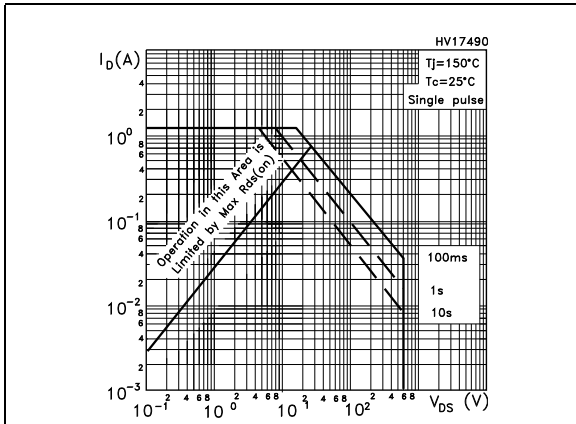


Figure 4. Safe operating area for SOT-223

Figure 5. Thermal impedance for SOT-223

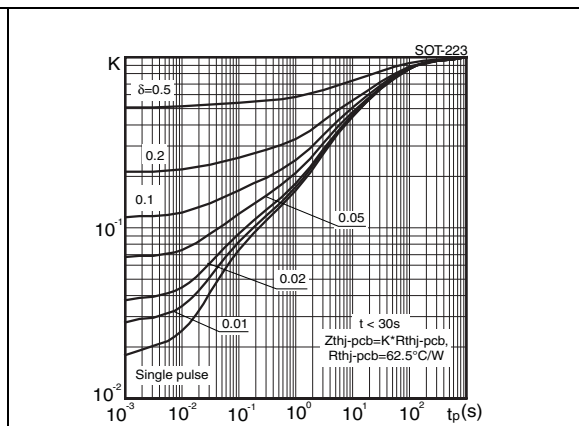
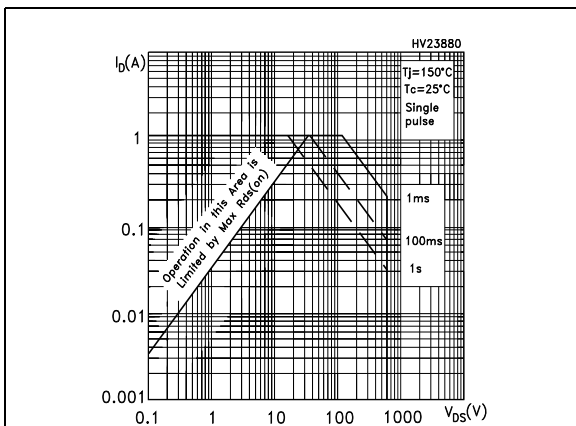


Figure 6. Output characteristics

Figure 7. Transfer characteristics

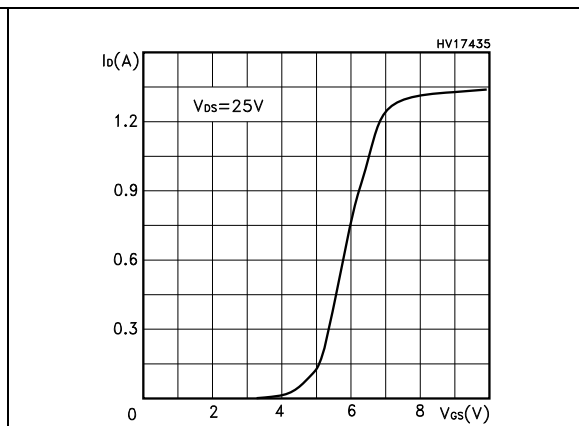
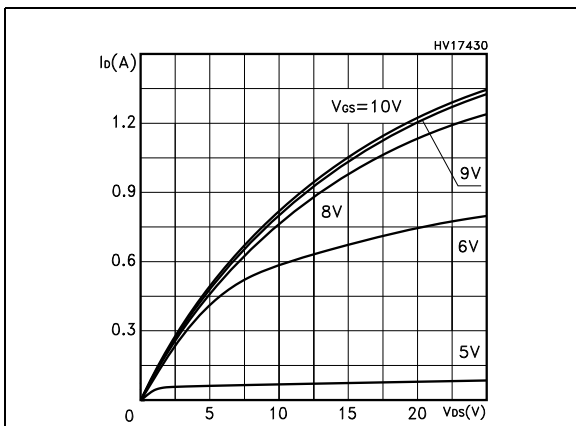


Figure 8. Transconductance

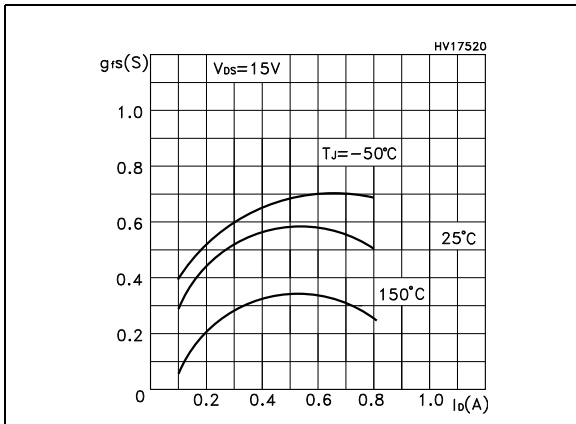


Figure 9. Static drain-source on resistance

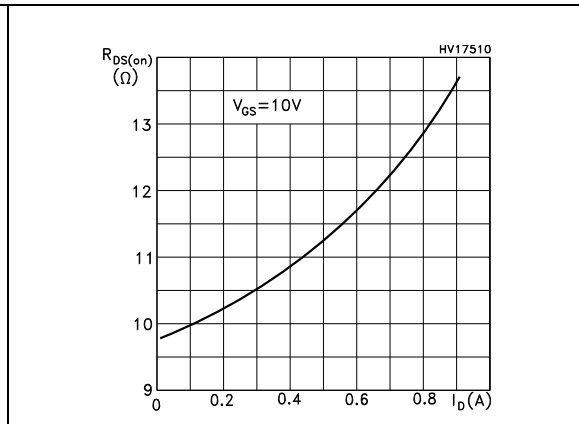


Figure 10. Gate charge vs gate-source voltage Figure 11. Capacitance variations

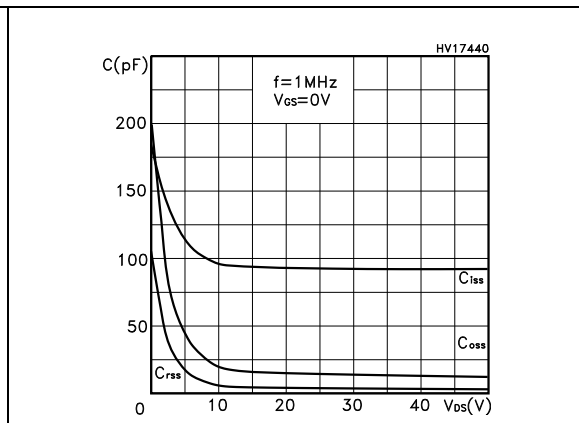
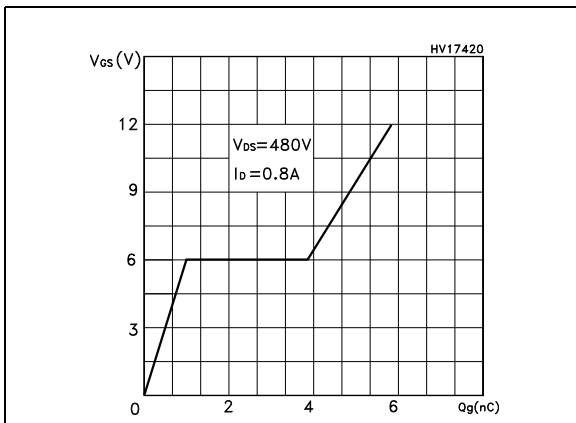


Figure 12. Normalized gate threshold voltage vs temperature

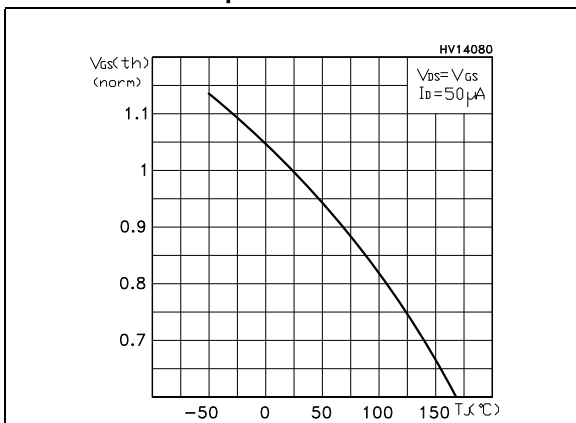


Figure 13. Normalized on resistance vs temperature

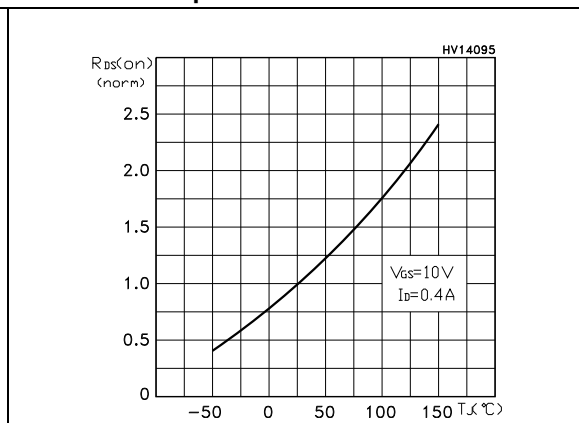


Figure 14. Source-drain diode forward characteristics

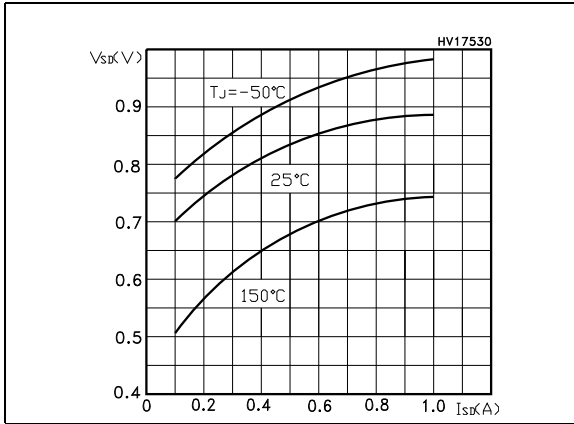


Figure 15. Normalized  $B_{VDSS}$  vs temperature

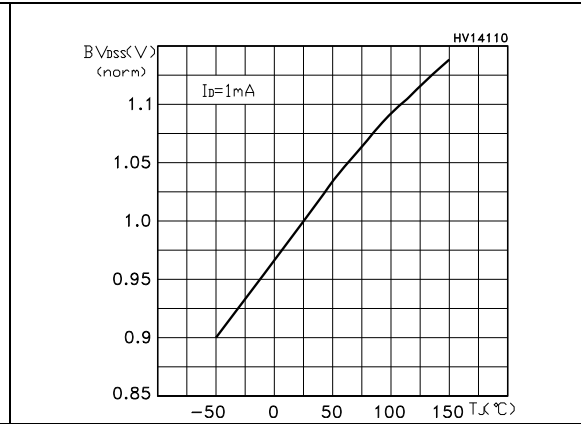


Figure 16. Maximum avalanche energy vs temperature

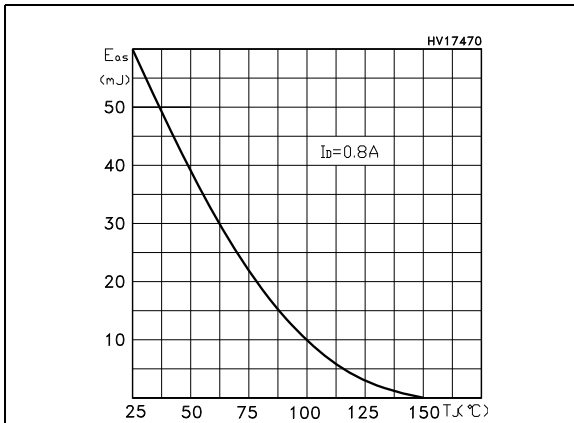
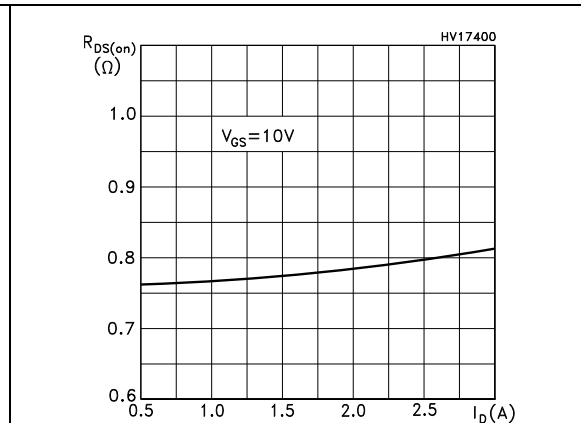


Figure 17. Max Id Current vs Tc





### 3 Test circuit

Figure 18. Switching times test circuit for resistive load

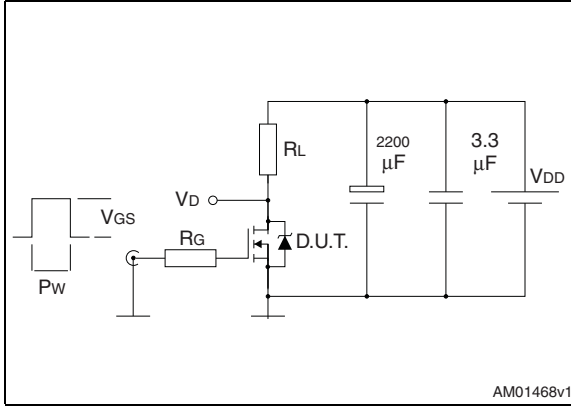


Figure 19. Gate charge test circuit

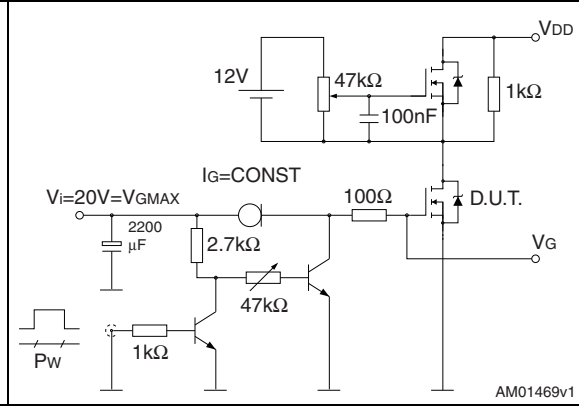


Figure 20. Test circuit for inductive load switching and diode recovery times

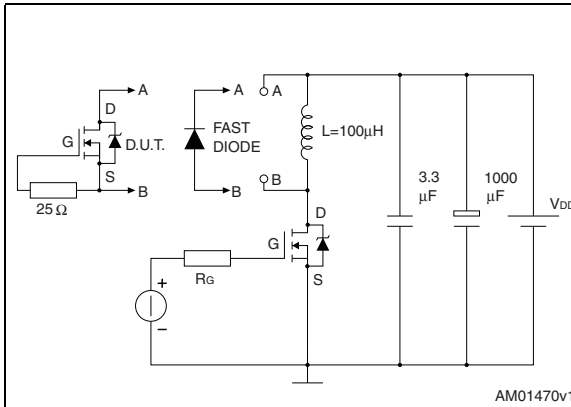


Figure 21. Unclamped inductive load test circuit

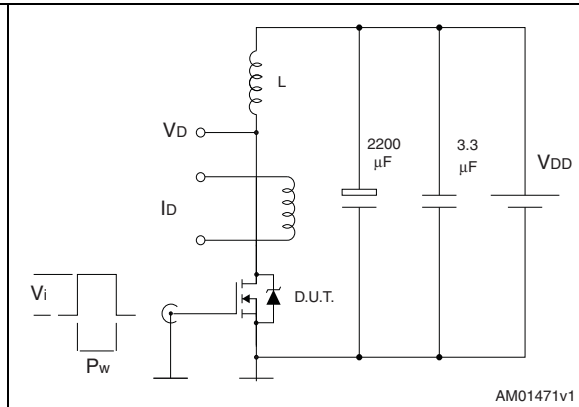


Figure 22. Unclamped inductive waveform

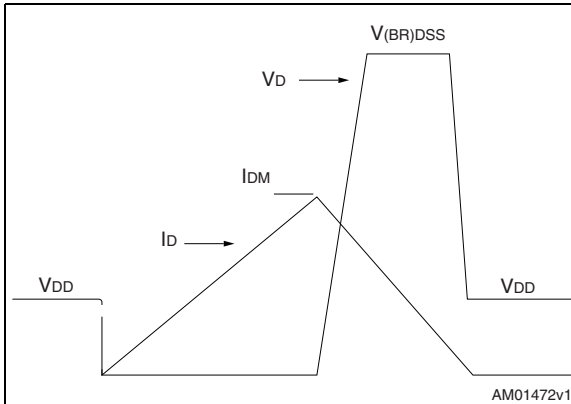
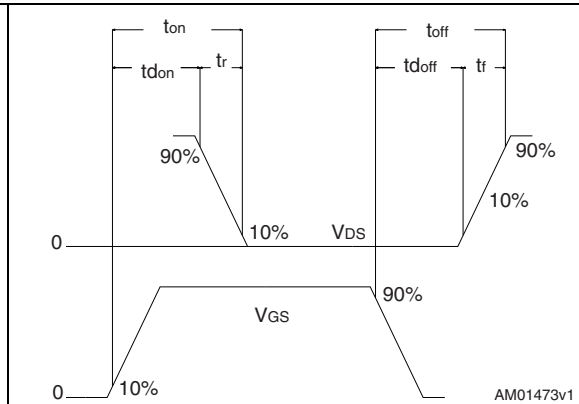


Figure 23. Switching time waveform



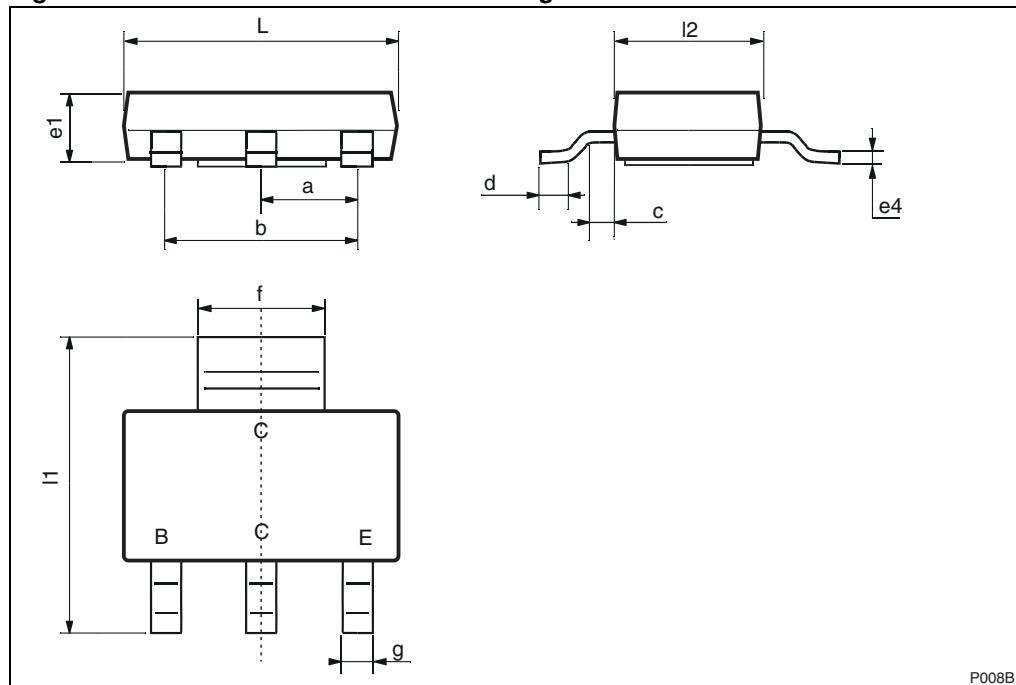
## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

Table 10. SOT-223 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
a	2.27	2.3	2.33
b	4.57	4.6	4.63
c	0.2	0.4	0.6
d	0.63	0.65	0.67
e1	1.5	1.6	1.7
e4			0.32
f	2.9	3	3.1
g	0.67	0.7	0.73
l1	6.7	7	7.3
l2	3.5	3.5	3.7
L	6.3	6.5	6.7

Figure 24. SOT-223 mechanical data drawing



P008B

Table 11. TO-92 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.32		4.95
b	0.36		0.51
D	4.45		4.95
E	3.30		3.94
e	2.41		2.67
e1	1.14		1.40
L	12.70		15.49
R	2.16		2.41
S1	0.92		1.52
W	0.41		0.56
V		5°	

Figure 25. TO-92 mechanical data drawing

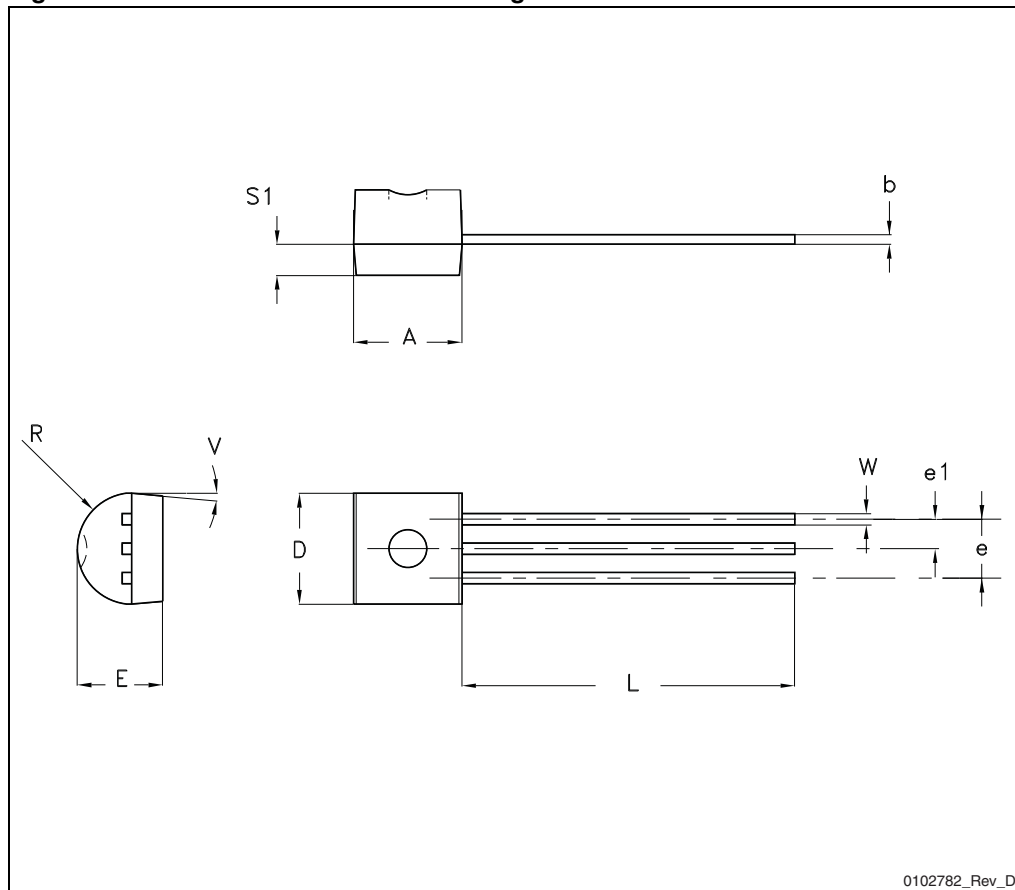
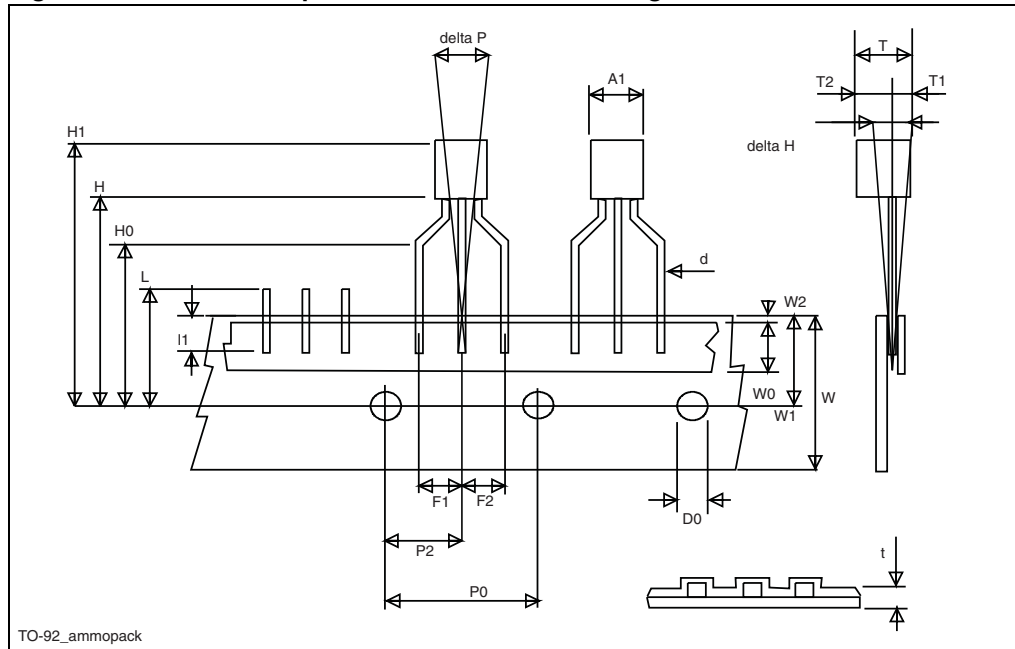


Table 12. TO-92 ammopack mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A1	4.45		4.95
T	3.30		3.94
T1			1.6
T2			2.3
d	0.41		0.56
P0	12.5	12.7	12.9
P2	5.65	6.35	7.05
F1, F2	2.44	2.54	2.94
delta H	-2		2
W	17.5	18	19
W0	5.7	6	6.3
W1	8.5	9	9.25
W2			0.5
H	18.5		20.5
H0	15.5	16	16.5
H1			25
D0	3.8	4	4.2
t			0.9
L			11
l1	3		
delta P	-1		1

Figure 26. TO-92 ammopack mechanical data drawing



## 5 Revision history

**Table 13. Revision history**

Date	Revision	Changes
19-Mar-2003	3	First electronic version
15-May-2003	4	Removed DPAK
09-Jun-2003	5	Final datasheet
17-Nov-2004	6	Inserted SOT-223
15-Feb-2005	7	Modified <a href="#">Figure 2</a> .
07-Sep-2005	8	Inserted ecopack indication
22-Feb-2006	9	The document has been reformatted
01-Jun-2007	10	Order code table on first page has been updated
19-Jul-2007	11	<a href="#">Table 1: Device summary</a> has been updated
05-Jan-2011	12	Corrected <a href="#">Figure 4: Safe operating area for SOT-223</a> and <a href="#">Figure 5: Thermal impedance for SOT-223</a>

**Please Read Carefully:**

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

**UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.**

**UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.**

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2011 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

[www.st.com](http://www.st.com)